Shantou Huashan Electronic Devices Co.,Ltd.

PNP DIGITAL TRANSISTOR

HA144T

APPLICATIONS

Switching Circuit，Interface Circuit.

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature·····150℃

P_C——Collector Dissipation·····300mW

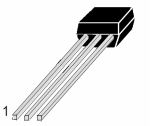
V_{CBO}——Collector-Base Voltage·····-50V

V_{CEO}——Collector-Emitter Voltage·····-50V

V_{EBO}——Emitter-Base Voltage·····-5V

I_C——Collector Current·····-100mA

TO-92S



1—Emitter，E
2—Collector,C
3—Base，B

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-50			V	I_C=-10μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-50			V	I_C=-0.1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	I_E=-50μA，I_C=0
I_{CBO}	Collector Cut-off Current			-0.1	μA	V_{CB}=-40V, I_E=0
I_{EBO}	Emitter Cut-off Current			-0.1	μA	V_{EB}=-5V, I_C=0
H_{FE}	DC Current Gain	100	250	600		V_{CE}=-5V, I_C=-1mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		-0.1	-0.3	V	I_C=-5mA, I_B=-0.5mA
$V_{I(off)}$	Input Off Voltage	-0.4	-0.55	-0.8	V	V_{CE}=-5V, I_C=-0.1mA
$V_{I(on)}$	Input On Voltage	-0.8	-2.0	-4.0	V	V_{CE}=-0.2V, I_C=-5mA
R1	Input Resistor	33	47	61	KΩ	
fr	Current Gain-Bandwidth Product		250		MHz	V_{CE}=-10V, I_C=-5mA
Cob	Output Capacitance		5.5		pF	V_{CB}=-10V, f=1MHz